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(54) **LIGHT-EMITTING DEVICE INCLUDING A
LIGHT-TRANSMITTING INTERCONNECT
LOCATED OVER A SUBSTRATE**

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(57)

ABSTRACT

A light-emitting device includes a light-transmitting substrate, a light-transmitting interconnect located over the substrate, an insulating layer located over the substrate and the interconnect, and an intermediate layer formed in at least a region of a lateral side of the interconnect that overlaps the insulating layer.

